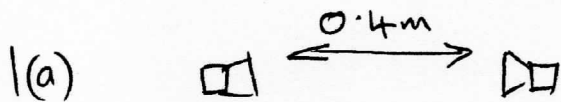


4813 2019



$$t_e = \frac{0.4}{340} = 1.18 \text{ ms}, \quad t_m = \frac{0.4}{240} = 1.667 \text{ ms}$$

$$\therefore \underline{\Delta t = 0.49 \text{ ms}}$$

(b) $Z_e = \rho r = 408 \text{ Ry/s}, \quad Z_m = 21.6 \text{ Ry/s}$

on Earth: $P_e = \frac{V^2/2}{R} \cdot \frac{4Z_e Z_m}{(Z_e + Z_m)^2} = 0.0298 \text{ W}$

$\frac{V^2/2}{R} = 0.0333$, $\frac{4Z_e Z_m}{(Z_e + Z_m)^2} = 0.895$

Received power @ transducer = $\eta \cdot \left[\frac{\pi d^2}{4} / \pi (0.4 \tan 10^\circ)^2 \right] \cdot P_e \cdot 10^{-0.4 \times 2.5}$

$\eta = 0.2$, $P_r = 5.37 \times 10^{-5} \text{ W}$

$10^{-0.4 \times 2.5} = 0.794$

Power coupled to transducer and converted to electrical signal

$$P_e = P_r \cdot \frac{4Z_e Z_m}{(Z_e + Z_m)^2} \cdot \eta = 9.61 \times 10^{-6} \text{ W} = \frac{V_r^2}{R}$$

with $R = 1500 \Omega$, $V_r = 0.120 \text{ V}_{\text{rms}} = 0.170 \text{ V}$ amplitude loaded
 $\times 2$ for open-cct = 0.34 V amplitude

On Mars: $\frac{4Z_e Z_m}{(Z_e + Z_m)^2} = 0.102 \therefore$ on Mars of Earth

power in sig. = $\times (0.102/0.895) \cdot 10^{\frac{0.4(2.5-2.1)}{10}} \times 0.118 = 50 \text{ voltage}$

amp² = $\times \sqrt{0.118} = \times 0.344 \Rightarrow$ 0.117 V amplitude

(c) On Mars, $10 \text{ m/s} @ 45^\circ \Rightarrow 7.07 \text{ m/s}$ along axis

Zero windspeed phase shift, $\phi = 0.4 \cdot \frac{150 \times 10^3}{240} \cdot 360^\circ = 9 \times 10^4$

\therefore with $\pm 7.07 \text{ m/s}$ $\Delta\phi = \pm \frac{7.07}{240} \cdot 9 \times 10^4 = \pm 2650^\circ$

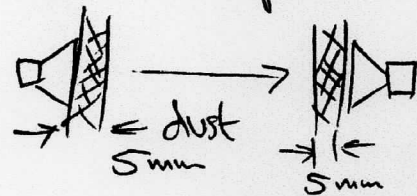
1 (d) $-63^{\circ}\text{C} \pm 80^{\circ}\text{C} \equiv 210\text{K} \pm 80\text{K}$ as the speed of sound $\propto \sqrt{T}$ then v changes by approx. $\pm 20\%$

Hence Z changes by $\frac{1}{T} \cdot \sqrt{T} = \frac{1}{\sqrt{T}}$ $T \uparrow, v \uparrow$
 $T \uparrow, Z \downarrow$

So, the measured windspeed will be less than actual with increasing temperature by $\sim 20\%$

The coupled powers due to changes in Z_m change by 20% each coupling hence as there are 2, the received power changes by 40% and so the signal voltage by 20% .
Higher temperature \rightarrow lower signals.

(e)



$$Z_d = 120 \times 500 = 6 \times 10^4 \text{ Ryls}$$

$$\text{transit time} = \frac{0.39}{240} + \frac{0.01}{500} = 1.645 \text{ ms}$$

Hence windspeed will be undermeasured by 1.3% (vs. 1.667ms)

Extra coupling losses thro' dust layers $Z_e \rightarrow Z_d, Z_d \rightarrow Z_m$

$$Z_e \rightarrow Z_d : \frac{4 \cdot 800 \cdot 6 \times 10^4}{(800 + 6 \times 10^4)^2} = 0.0519$$

$$Z_d \rightarrow Z_m : \frac{4 \cdot 21.6 \cdot 6 \times 10^4}{(21.6 + 6 \times 10^4)^2} = 1.44 \times 10^{-3}$$

$$\text{Attenuation thro' dust} = 66 \times 0.01 = 0.66 \text{ dB}$$

$$\Rightarrow \times 10^{-\frac{0.66}{10}} = \times 0.859$$

$$\therefore \text{power coupling loss} = 0.0519^2 \cdot (1.44 \times 10^{-3})^2 \cdot 0.859$$

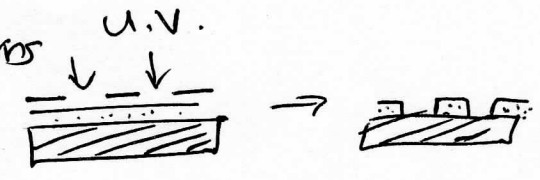
$$= \times 4.80 \times 10^{-9} ! \quad (\text{a lot})$$

$$\text{So signal amplitude} \times \sqrt{4.8 \times 10^{-9}} = \times 6.93 \times 10^{-5}$$

$$\text{Hence } 0.117 \text{ V} \rightarrow \underline{8.1 \mu\text{V}} \quad (\text{still measurable though}).$$

2(a) MEMS processes:

- photolithography to define patterns
- expose spun-on photoresist to U.V. through mask
- exposed areas dissolve away in NaOH developer
- then etch underlayer/substrate: plasma or KOH
- hinge formed by boron doping, slowing down hot KOH etch. silicon χ tal plane etches @ 35° to give tapered edges.
- glass etched with HF solution to form recess
- electrode patterned in evaporated or sputtered Al layer, etched with acidic soln.
- glass and silicon bonded with pressure + temperature to fusion bond @ 500°C



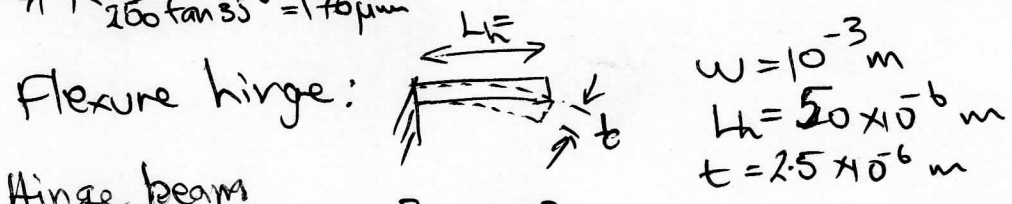
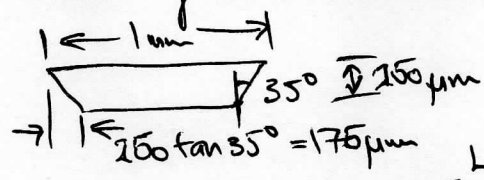
(b) (i) zero def: $C = \frac{A\epsilon}{d} = \frac{10^{-6} \cdot 8.854 \times 10^{-12}}{100 \times 10^{-6}} = 0.088 \text{ pF}$

5° of tilt: mid-point deflection = $\delta \frac{0.5 \text{ mm}}{50} = 0.0437 \text{ mm}$

\therefore average gap, d is now $(0.1 - 0.0437) = 0.056 \text{ mm}$

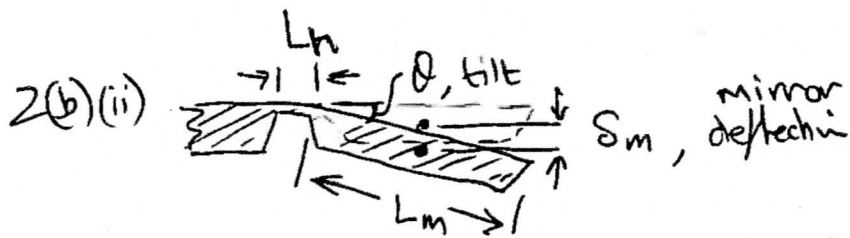
$\therefore C = \frac{0.1}{0.056} \times 0.088 = 0.156 \text{ pF}$ (assuming fringe fields compensate for edge angles)

(ii) Mass of mirror: $\Rightarrow 2.5(1 - 0.175)^2 \cdot 10^{-6} \cdot 10^{-7} \cdot 2330 \text{ kg} = 3.96 \times 10^{-10} \text{ kg}$



Hinge beams
 Deflection, $\delta_b = \frac{FL_h^3}{3EI} + \frac{ML_h^2}{2EI}$ $I = \frac{1}{12} wt^3 = 1.30 \times 10^{-24} \text{ m}^4$
 $E = 110 \times 10^9 \text{ N m}^{-2}$

Assume $M = F \times 0.5 \times 10^{-3}$ (centre of force is $1/2$ way along mirror)
 $F = \text{force on mirror}$ $L_m/2$



Mirror deflection, $\delta_m = \delta_b + \frac{L_m}{2} \theta$

$$\theta = \frac{FL_h^2}{2EI} + \frac{FL_m L_h}{2EI}$$

$$\therefore \delta_m = \frac{FL_h^3}{3EI} + F \frac{L_m L_h^2}{2EI} + \frac{FL_h^2 L_m}{2EI} + \frac{FL_m L_h}{2EI}$$

$$\delta_m = \frac{FL_h}{EI} \left(\frac{L_h^2}{3} + \frac{L_m L_h}{4} + \frac{L_h L_m}{4} + \frac{L_m^2}{4} \right)$$

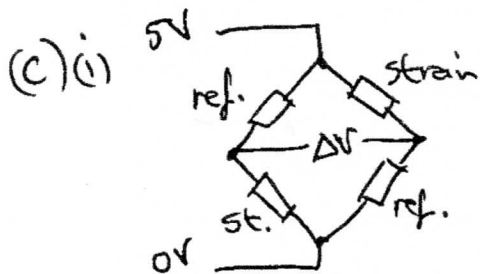
dominant term (90%)

with $L_h = 50 \times 10^{-3} \text{ m}$, $L_m = 10^{-3} \text{ m}$, $E = 110 \times 10^9 \text{ Nm}^2$, $I = 1.3 \times 10^{-21} \text{ m}^4$

$\delta_m = F \cdot 0.096$ hence spring constant $k = \frac{1}{0.096} = 10.4 \text{ N/m}$

\therefore resonant freq. = $\frac{1}{2\pi} \sqrt{\frac{k}{m}} = \frac{1}{2\pi} \sqrt{\frac{10.4}{3.96 \times 10^{-7}}} = 816 \text{ Hz}$

\therefore settling time $\approx \frac{Q}{f_{res}} = 49 \text{ ms}$



$$\Delta V = \frac{2}{4} \times \epsilon \times G.F. \times V_s \quad G.F. = 35 \quad V_s = 5V$$

$$\frac{\sigma}{y} = \frac{M}{I} = \frac{\epsilon E}{y} \quad E = 110 \times 10^9 \text{ Nm}^2$$

$$y = 1.25 \times 10^{-6} \text{ m}$$

$$L_h = 50 \times 10^{-6} \text{ m}$$

@ max. deflection of 5° , $\theta = \frac{M L_h}{EI} = \frac{5\pi}{180}$

$$\therefore M = \frac{5\pi}{180} \cdot \frac{EI}{L_h} = \frac{\epsilon EI}{y} \therefore \epsilon = \frac{5\pi}{180} \frac{y}{L_h} = 2.18 \times 10^{-3}$$

$$\therefore \Delta V = 5 \times 35/2 \epsilon = 87.5 \epsilon = 0.191 V$$

Noise voltage $v_n = \sqrt{4kTRB}$ with $R = 10^4 \Omega$, $B = \frac{816}{40} \text{ Hz}$

$v_n = 0.058 \text{ } \mu\text{V}_{\text{rms}}$ for S/N of say 10:1 then min. deflection

resolution = $5^\circ \times \frac{0.058 \times 10^{-6} \times 10}{0.191} = 1.5 \times 10^{-5} \text{ degrees}$

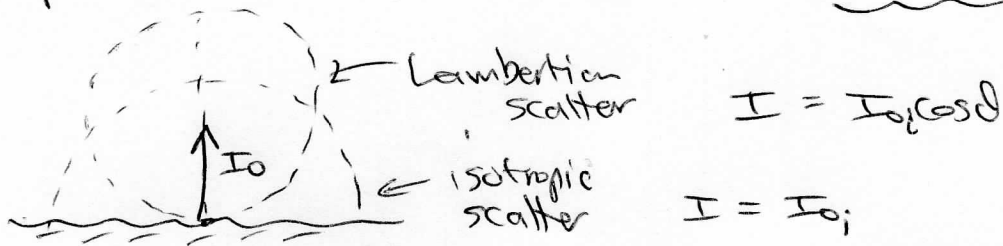
(ii) with capacitive drive, the tilt is non-linear with voltage as force is prop. to V^2 so strain gauges can provide linear feedback signal - also to improve dynamic response + damping.

3(c) contd.

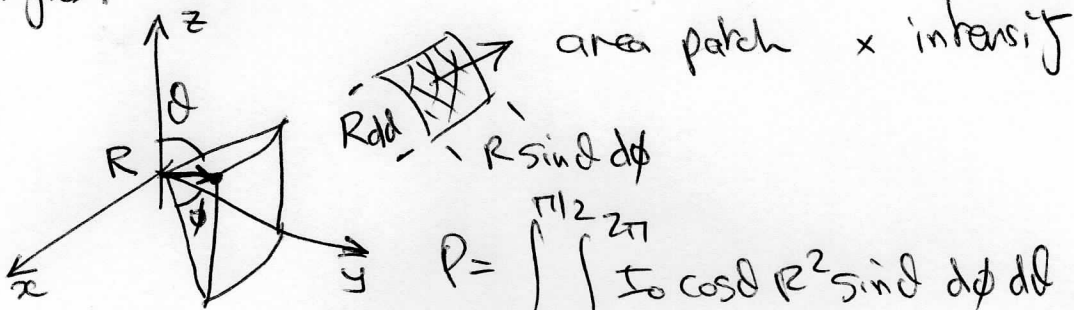
$$\text{scattered light} = 35\% \times 5W = 1.75W$$

$$\therefore \text{photocurrent} = 0.8 \times 1.75 \times 5 \times 10^{-7} = \underline{\underline{7 \times 10^{-7} A}}$$

(d)



For same total emitted power, integrate $I_0 \cos \theta$ over hemisphere to determine total power back-scattered over all angles.



$$\therefore P = I_0 R^2 2\pi \int_0^{\pi/2} \sin \theta \cos \theta d\theta = I_0 R^2 2\pi \int_0^{\pi/2} \frac{1}{2} \sin 2\theta d\theta$$

$$\therefore P = I_0 R^2 2\pi \left[-\frac{1}{2} \frac{\cos 2\theta}{2} \right]_0^{\pi/2} = I_0 \pi R^2$$

$$\text{So, at } 45^\circ \text{ then Lambertian intensity} = \frac{P \cos 45^\circ}{\pi R^2} = \frac{1/\sqrt{2} P}{\pi R^2} = I_L$$

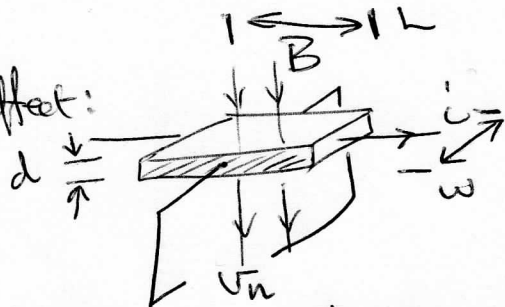
$$\text{whereas in the isotropic case } I_i = \frac{P}{2\pi R^2} \quad \therefore \underline{\underline{\frac{I_L}{I_i} = \sqrt{2}}}$$

(Signal is larger in Lambertian case)

(e) To ensure immunity to ambient light:

- use a narrow-band optical filter on the photo-diode, matched to pass the laser light only
- modulate the laser and use synchronous detection so that the signal only responded to the modulation-freq.
- shade the photo-diode field of view to avoid ambient light being seen eg. avoid direct view of the sun (reduces shot noise)

4(a) Hall effect:

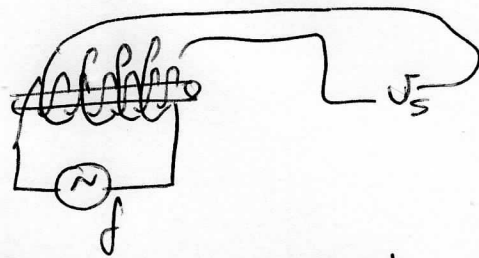


semiconductor slice through which current passes. Orthogonal magnetic field deflects moving carriers.

Current carriers are deflected sideways by Lorentz force $f = Bev_d$ when moving at drift velocity v_d . The carriers accumulate on edge faces to build up transverse electric field which balances Lorentz force in equilibrium state so $Ee = Bev_d$, $E = \frac{v_{Hall}}{w}$, $v_d = \mu \frac{V_s}{L}$

Fluxgate:

One (or two) cores are driven into saturation by coil with ac. excitation.



This periodically saturates the core in the ad -ve direction - if an external field also couples into the core, this introduces an offset in the timings of the ad -ve saturation sweeps. These transitions effectively gate the external field into/out of the core as the permeability is switched high/low. A pick-up coil around the core is induced with a $2f$ signal proportional to the applied external field. Using 2 cores inside the pick-up coil, driven in anti-phase, cancels direct coupling of f drive - hence a clearer $2f$ signal is seen. The $2f$ is detected and demodulated by a synchronous detection circuit set to $2f$, with phase shift to maximize signal.

(b) Cores ϕ 1mm, $L = 40\text{mm}$ $D = \frac{[\ln 80 - 1]}{40^2} = \frac{1}{473}$

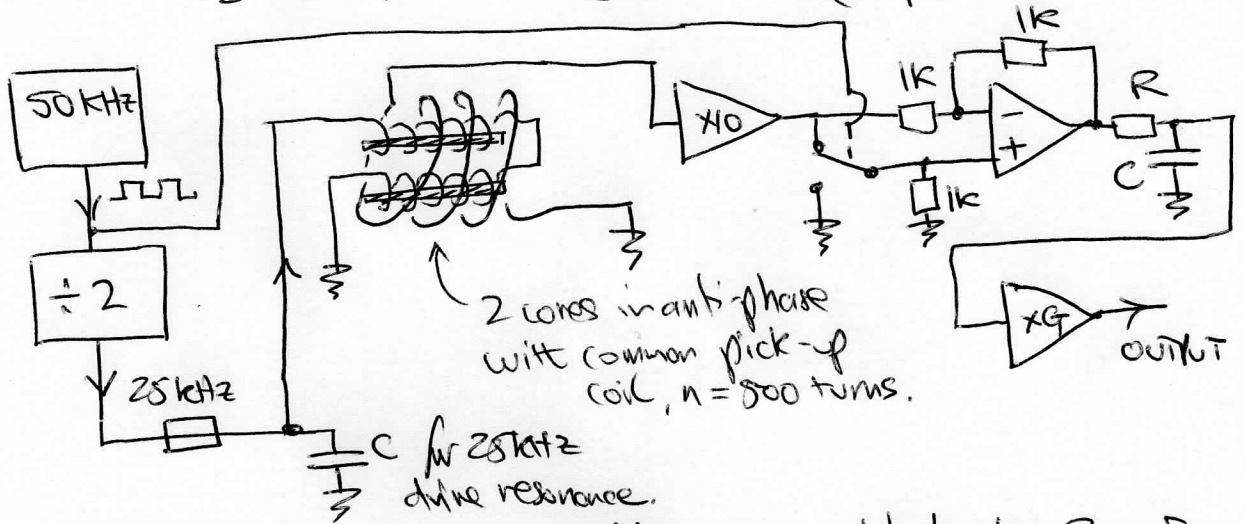
\therefore internal flux density $B = B_{ext} \times 473 = 0.71\text{mT}$

Induced 2nd harmonic voltage $V = V_2 \sin 4\pi f t$, so $\int V dt = BAN$

$\therefore \int V dt = BAN = \left[\frac{V_2 \cos 4\pi f t}{4\pi f} \right]_0^{1/4f} = \frac{V_2}{2\pi f}$ so signal amplitude

$V_2 = 2\pi n f BA$, with $n=500$, $f=25 \times 10^3\text{Hz}$, $A = \frac{\pi \cdot 10^{-6}}{4}$

4(b) contd. $V_2 = 0.0438 \text{ V}$ @ 50 kHz (amplitude with 2-cores)



The RC will average the rectified V_2 amplitude to $\frac{2}{\pi} \times V_2$

Hence final gain $G = \frac{1}{0.0438 \times 10 \times 2/\pi} = 3.59$

choose R & C for 100 Hz BW eg: $100 = \frac{1}{2\pi RC}$ $R = 10 \text{ k}\Omega$ $C = 16 \mu\text{F}$

(c) (i) with cores end-to-end $\frac{l}{d} = 80$, $D = \frac{1}{1570}$ \therefore flux density is concentrated by $\times 1570 \Rightarrow 2.36 \text{ mT}$

(ii) $B \times v_d = \frac{\phi v_h}{w} = \frac{B \mu v_s}{L} \therefore \frac{v_h}{B} = \frac{w \mu v_s}{L} = 0.8 \text{ V/T}$

$\therefore v_h = 2.36 \times 0.8 \times 10^{-3} \text{ V} = 1.89 \text{ mV}$

(iii) Hall sensor resistance = $\frac{\rho L}{wd} = 1000 \Omega$

Assuming linear excess carrier conc. n_0 vs x , dist. $n = \frac{2n_0 x}{w}$

Diffusion flux across centre-line $F = -D \frac{dn}{dx}$, $D = \mu kT/q$

where $\frac{dn}{dx} = \frac{2n_0}{w}$ \therefore total carriers diffusing back $\frac{dN}{dt} = -D \frac{2n_0}{w} Ld$, $n_0 = \frac{4N}{wLd}$

as total $N = \int_0^{w/2} Ld \frac{2n_0}{w} x dx = \frac{n_0 w L d}{4}$, $\frac{dN}{dt} = -\frac{8DN}{w^2}$ 1st order D.E.

Soln of form $N = N_0 e^{-t/\tau}$ with $\tau = w^2/8D$

$\therefore f_{-3dB} \approx \frac{1}{2\pi\tau} = \frac{4D}{\pi w^2} = \frac{4\mu kT}{\pi q w^2} = 58.6 \text{ kHz}$

and thermal noise voltage, $v_n = \sqrt{4kTRB} = 0.99 \mu\text{V rms}$